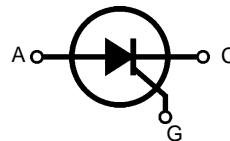


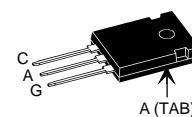
Phase Control Thyristor

V_{RRM} = 800-1600 V
I_{T(RMS)} = 75 A
I_{T(AV)M} = 48 A

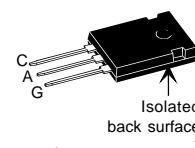
V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
900	800	CS 45-08io1
1300	1200	CS 45-12io1
1700	1600	CS 45-16io1 CS 45-16io1R



TO-247 AD
Version io1



ISOPLUS 247™
Version io1R



* Patent pending

C = Cathode, A = Anode, G = Gate

Symbol	Conditions	Maximum Ratings		
I _{T(RMS)}	T _{VJ} = T _{VJM}	75	A	
I _{T(AV)M}	T _C = 75°C; 180° sine	48	A	
I _{TSM}	T _{VJ} = 45°C V _R = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520 560	A A
	T _{VJ} = T _{VJM} V _R = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	460 500	A A
I ² t	T _{VJ} = 45°C V _R = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350 1300	A ² s A ² s
	T _{VJ} = T _{VJM} V _R = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1050 1030	A ² s A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50 Hz, t _p = 200 µs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/µs	repetitive, I _T = 40 A non repetitive, I _T = I _{T(AV)M}	150 500	A/µs A/µs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GR} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/µs
P _{GM}	T _{VJ} = T _{VJM} I _T = I _{T(AV)M}	t _p = 30 µs t _p = 300 µs	10 5 0.5	W W W
P _{G(AV)}				
V _{RGM}			10	V
T _{VJ}			-40...+140	°C
T _{VJM}			140	°C
T _{stg}			-40...+125	°C
M _d	Version io1: mounting torque M3		0.8...1.2	Nm
F _c	Version io1R: mounting force with clip		20...120	N
V _{ISOL} *	50/60 Hz, RMS, t = 1 minute, leads-to-tab		2500	V~
Weight			6	g

* Version io1R only

Data according to IEC 60747
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Conditions	Characteristic Values		
I_R, I_D	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5	mA
V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.64	V
V_{TO}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85	V	
r_T		11	mΩ	
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	1.5	V
	$T_{VJ} = -40^\circ\text{C}$	\leq	1.6	V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	100	mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	200	mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	\leq	0.2	V
I_{GD}		\leq	10	mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	150	mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	100	mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	\leq	2	μs
R_{thJC}	DC current		0.62	K/W
R_{thJH}	DC current		0.82	K/W
a	Max. acceleration, 50 Hz		50	m/s ²

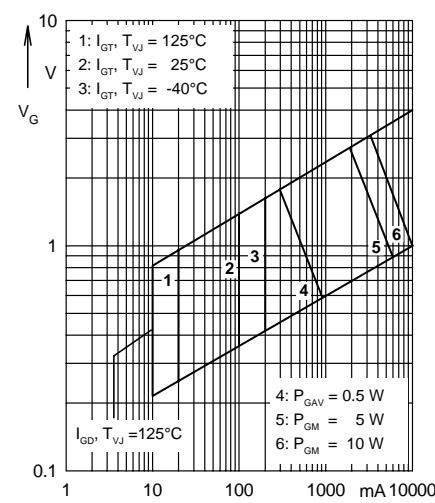
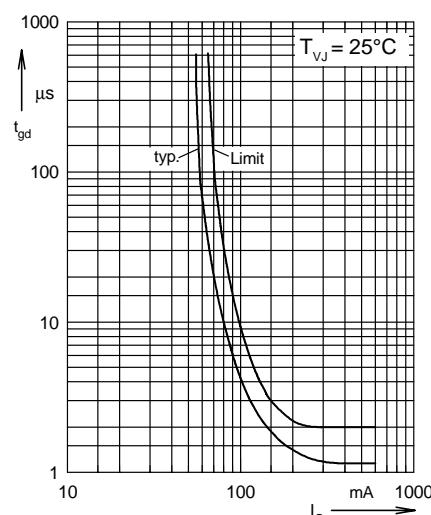
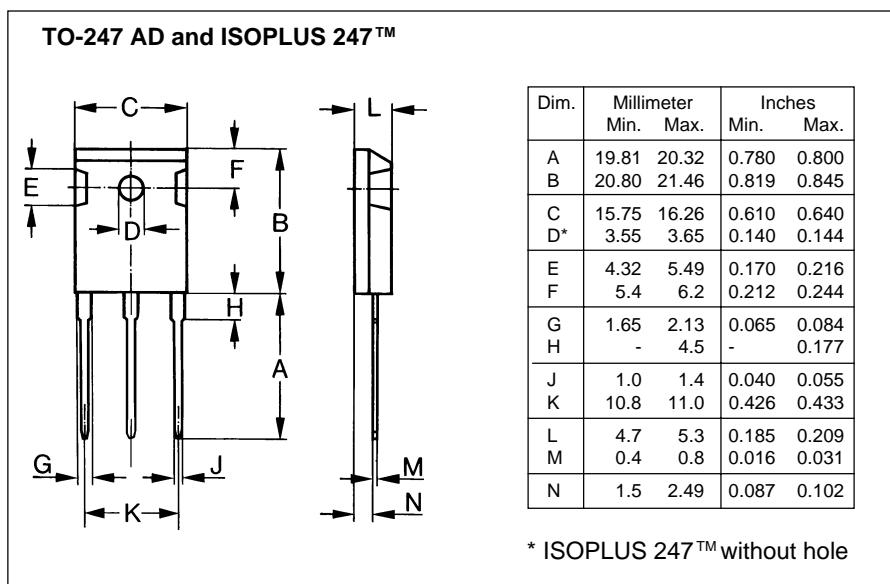


Fig. 1 Gate trigger range

Fig. 2 Gate controlled delay time t_{gd} 

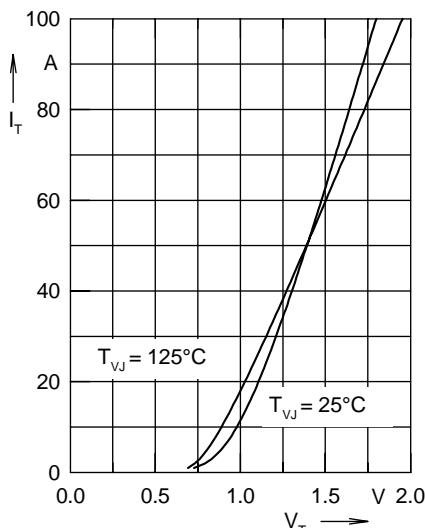


Fig. 3 Forward characteristics

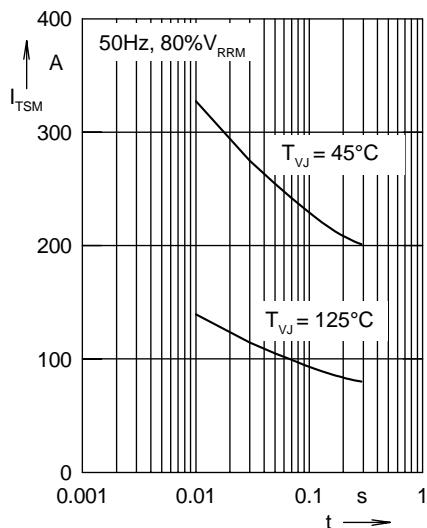


Fig. 4 Surge overload current
 I_{TSM} : crest value, t : duration

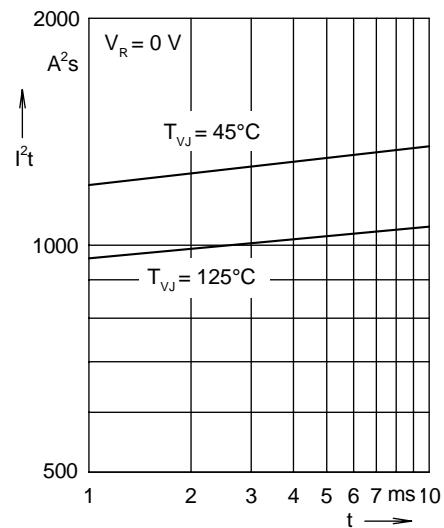


Fig. 5 I^2t versus time (1-10 ms)

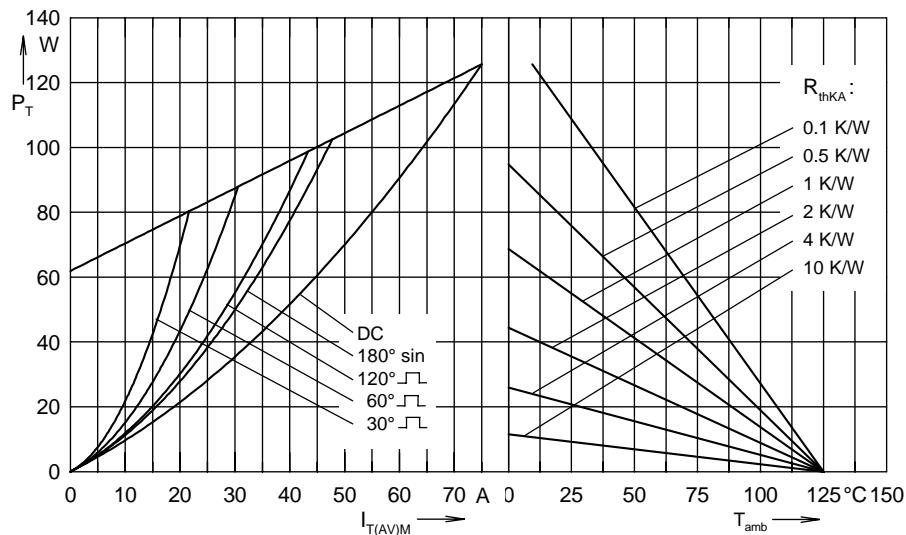


Fig. 6 Power dissipation versus forward current and ambient temperature

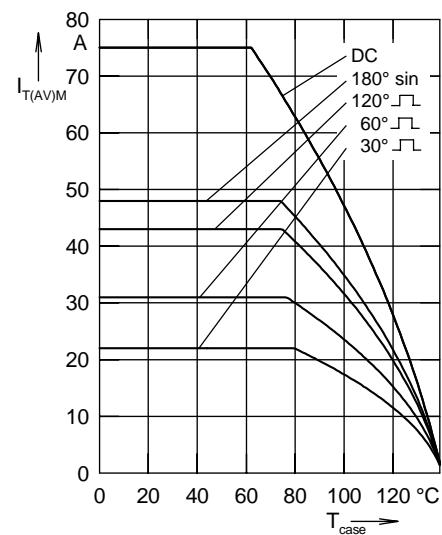


Fig. 7 Max. forward current at case temperature

R_{thJC} for various conduction angles d :

d	R_{thJC} (K/W)
DC	0.62
180°	0.71
120°	0.748
60°	0.793
30°	0.817

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.206	0.013
2	0.362	0.118
3	0.052	1.488

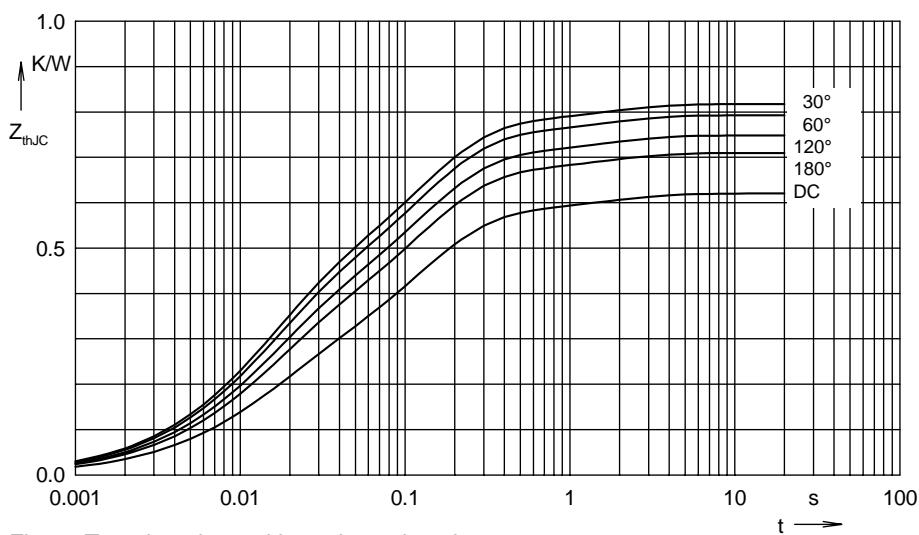


Fig. 8 Transient thermal impedance junction to case